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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HVD141

Silicon Epitaxial Trench Pin Diode for Antenna Switching



ADE-208-1087 (Z)

Rev. 0
Jan. 2001

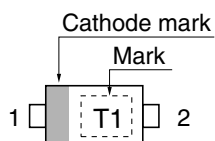
Features

- Low capacitance. ($C = 0.82 \text{ pF max}$)
- Low forward resistance. ($r_f = 0.8 \Omega \text{ max}$)
- Super small Flat Package (SFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVD141	T1	SFP

Pin Arrangement



1. Cathode
2. Anode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Power dissipation	Pd	150	mW
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	0.1	μA	$V_R = 30\text{ V}$
Forward voltage	V_F	—	—	1.0	V	$I_F = 10\text{ mA}$
Capacitance	C	—	—	0.82	pF	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$
Forward resistance	r_f	—	—	0.8	Ω	$I_F = 10\text{ mA}$, $f = 100\text{ MHz}$

Note: Please do not use the soldering iron due to avoid high stress to the SFP package.

Main Characteristic

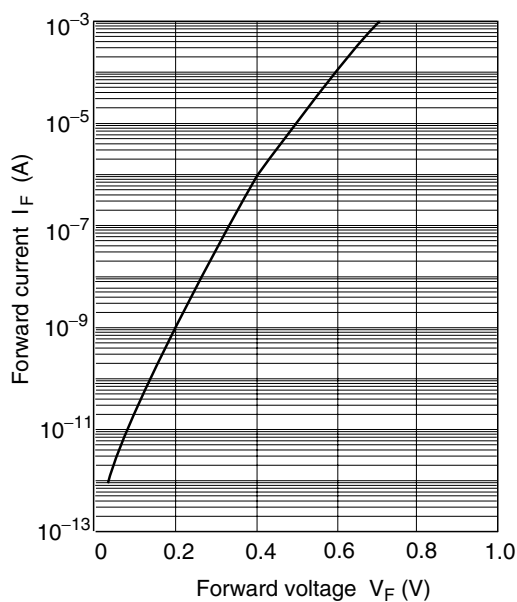


Fig.1 Forward current Vs. Forward voltage

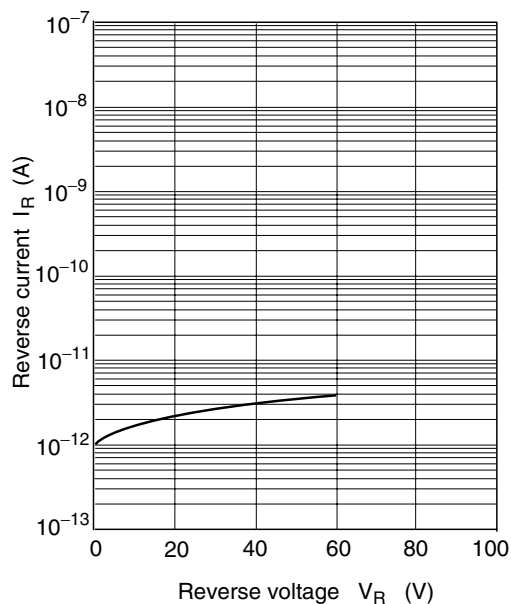


Fig.2 Reverse current Vs. Reverse voltage

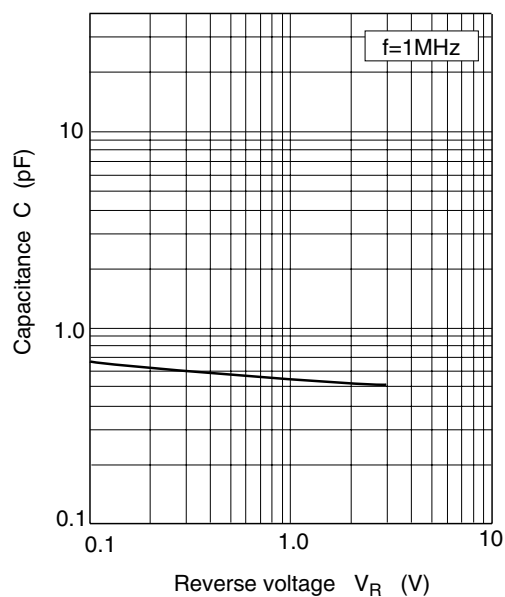


Fig.3 Capacitance Vs. Reverse voltage

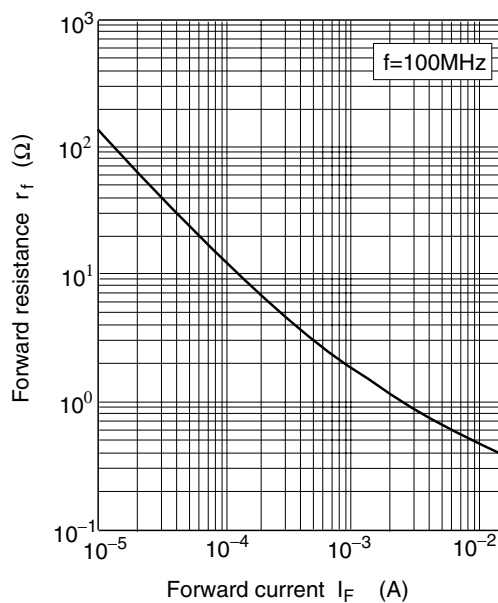


Fig.4 Forward resistance Vs. Forward current

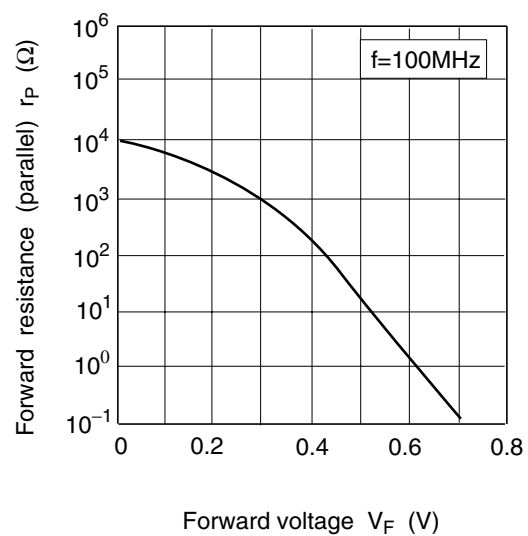
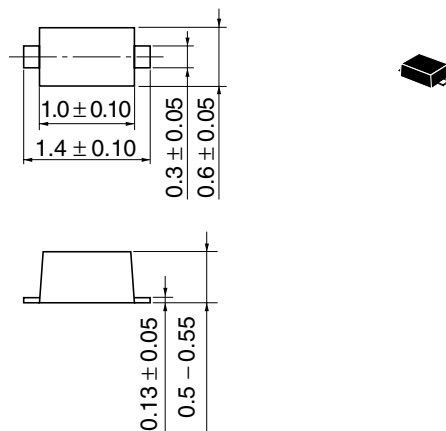


Fig.5 Forward resistance (parallel) Vs. Forward voltage

Package Dimensions

Unit: mm



Hitachi Code	SFP
JEDEC	—
EIAJ	—
Mass (reference value)	0.0010 g

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Sales Offices**HITACHI****Hitachi, Ltd.**

Semiconductor & Integrated Circuits

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia	: http://sicapac.hitachi-asia.com
	Japan	: http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc.	Hitachi Europe Ltd.
179 East Tasman Drive	Electronic Components Group
San Jose, CA 95134	Whitebrook Park
Tel: <1> (408) 433-1990	Lower Cookham Road
Fax: <1> (408) 433-0223	Maidenhead
	Berkshire SL6 8YA, United Kingdom
	Tel: <44> (1628) 585000
	Fax: <44> (1628) 585200

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road
Hung-Kuo Building
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: http://semiconductor.hitachi.com.hk

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